

N-channel MOS-FET			
300V	0,2Ω	20A	125W

2SK2473-01

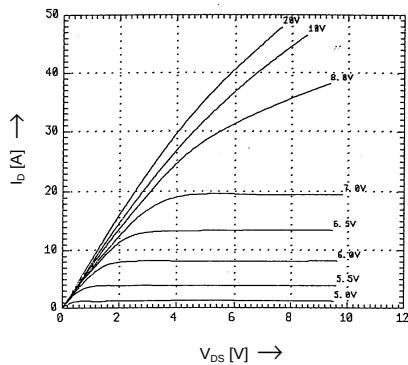
FAP-II Series

FUJI
ELECTRIC

> Characteristics

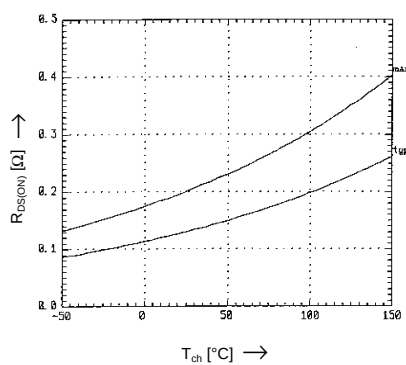
Typical Output Characteristics

$I_D = f(V_{DS})$; 80μs pulse test; $T_C = 25^\circ\text{C}$



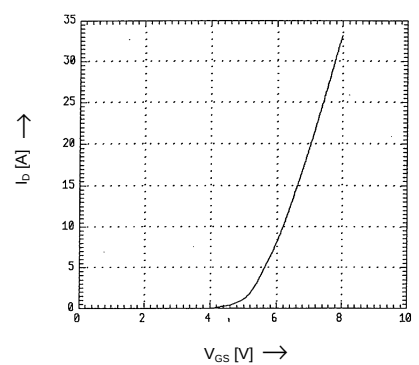
Drain-Source On-State Resistance vs. T_{ch}

$R_{DS(on)} = f(T_{ch})$; $I_D = 10\text{A}$; $V_{GS} = 10\text{V}$



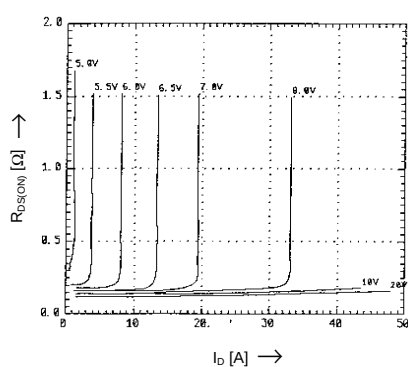
Typical Transfer Characteristics

$I_D = f(V_{GS})$; 80μs pulse test; $V_{DS} = 25\text{V}$; $T_{ch} = 25^\circ\text{C}$



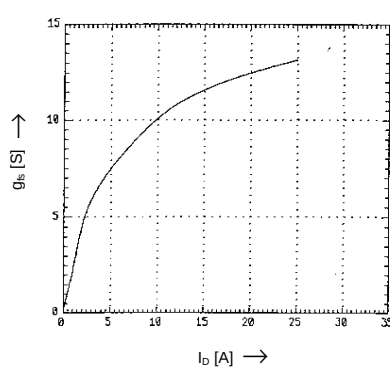
Typical Drain-Source On-State-Resistance

$R_{DS(on)} = f(I_D)$; 80μs pulse test; $T_C = 25^\circ\text{C}$



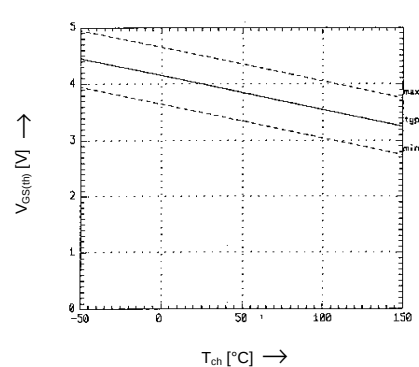
Typical Transconductance

$g_{fs} = f(I_D)$; 80μs pulse test; $V_{DS} = 25\text{V}$; $T_{ch} = 25^\circ\text{C}$



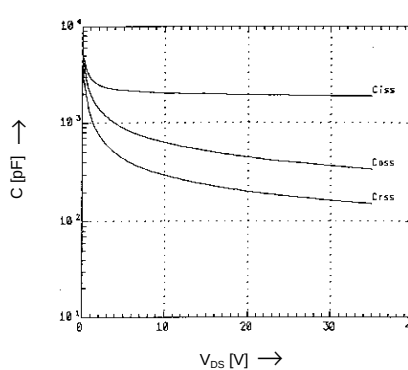
Gate Threshold Voltage

$V_{GS(th)} = f(T_{ch})$; $I_D = 1\text{mA}$; $V_{DS} = V_{GS}$



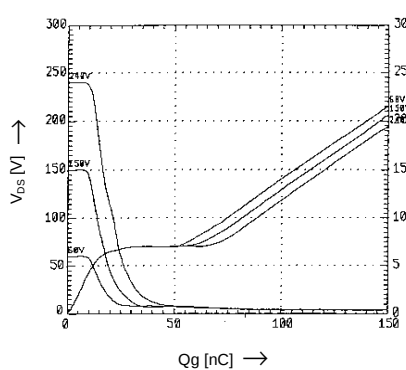
Typical Capacitances

$C = f(V_{DS})$; $V_{GS} = 0\text{V}$; $f = 1\text{MHz}$



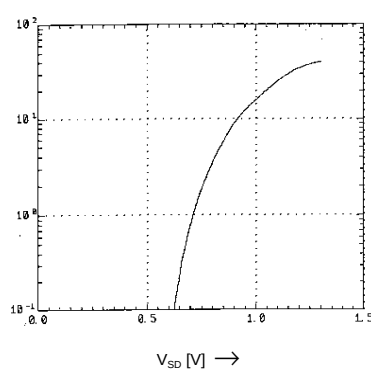
Typical Gate Charge Characteristics

$V_{GS} = f(Q_g)$; $I_D = 20\text{A}$



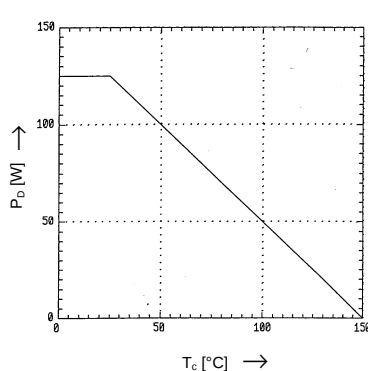
Forward Characteristics of Reverse Diode

$I_F = f(V_{SD})$; 80μs pulse test



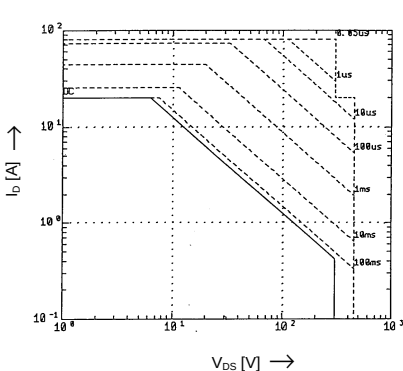
Power Dissipation

$P_D = f(T_C)$



Safe Operation Area

$I_D = f(V_{DS})$; $D = 0.01$; $T_C = 25^\circ\text{C}$



$Z_{th(ch-q)}$ [K/W]

Transient Thermal impedance

$Z_{th(ch)} = f(t)$ parameter: $D = t/T$

